TOSHIBA Field Effect Transistor Silicon N Channel MOS Type  $(\pi - MOSVII)$ 

# **TK12A60D**

#### **Switching Regulator Applications**

• Low drain-source ON resistance: RDS (ON) =  $0.45 \Omega$  (typ.)

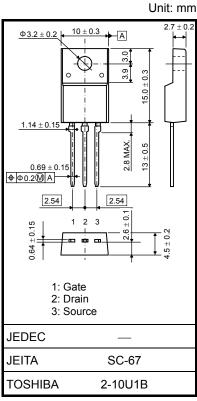
• High forward transfer admittance:  $|Y_{fs}| = 7.5 \text{ S (typ.)}$ 

• Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 600 \text{ V)}$ 

• Enhancement-mode:  $V_{th} = 2.0 \text{ to } 4.0 \text{ V (VDS} = 10 \text{ V, ID} = 1 \text{ mA)}$ 

#### Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	600	V	
Gate-source voltage		$V_{GSS}$	±30	V	
Drain current	DC (Note 1)	I <sub>D</sub>	12	Α	
	Pulse (Note 1)	I <sub>DP</sub>	48	A	
Drain power dissipation	on (Tc = 25°C)	P <sub>D</sub>	45	W	
Single pulse avalanche energy (Note 2)		E <sub>AS</sub>	359	mJ	
Avalanche current		I <sub>AR</sub>	12	Α	
Repetitive avalanche energy (Note 3)		E <sub>AR</sub>	4.5	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C	



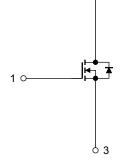
Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R <sub>th (ch-c)</sub>	2.78	°C/W
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	62.5	°C/W

Internal Connection



Note 1: Please use devices on conditions that the channel temperature is below 150°C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 4.36 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 12 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.

Start of commercial production 2009-01

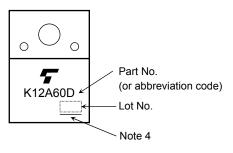
### **Electrical Characteristics (Ta = 25°C)**

Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μА
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V	_	_	10	μА
Drain-source brea	akdown voltage	V (BR) DSS	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	600	_	_	V
Gate threshold vo	oltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	2.0	_	4.0	V
Drain-source ON	resistance	R <sub>DS (ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 6 A	_	0.45	0.55	Ω
Forward transfer	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 6 A	1.9	7.5	_	S
Input capacitance		C <sub>iss</sub>		_	1800	_	
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	9	_	pF
Output capacitance		Coss		_	190	_	
Switching time	Rise time	t <sub>r</sub>	$\begin{array}{c c} 10 \text{ V} & \text{I}_D = 6 \text{ A} & \text{V}_{\text{OUT}} \\ \hline \text{VGS} & \text{O} & \text{V} \\ \hline 50 \Omega & \text{RL} = 33 \Omega \\ \hline \end{array}$	_	40	_	. ns
	Turn-on time	t <sub>on</sub>			80	_	
	Fall time	t <sub>f</sub>			15	_	
	Turn-off time	t <sub>off</sub>	Duty ≤ 1%, t <sub>W</sub> = 10 μs		110	_	
Total gate charge		Qg		_	38	_	
Gate-source charge		Q <sub>gs</sub>	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 12 \text{ A}$	_	24	_	nC
Gate-drain charge		Q <sub>gd</sub>		_	14	_	

## Source-Drain Ratings and Characteristics (Ta = 25°C)

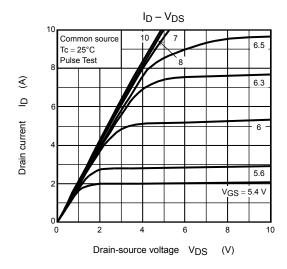
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	_	_	_	12	Α
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	_	_	_	48	Α
Forward voltage (diode)	V <sub>DSF</sub>	I <sub>DR</sub> = 12 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	$I_{DR} = 12 \text{ A}, V_{GS} = 0 \text{ V},$	_	1200	_	ns
Reverse recovery charge	Q <sub>rr</sub>	dI <sub>DR</sub> /dt = 100 A/μs	_	13	_	μС

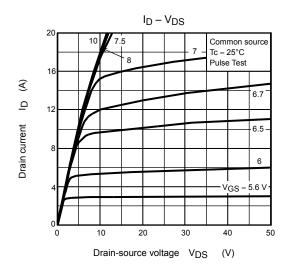
### Marking

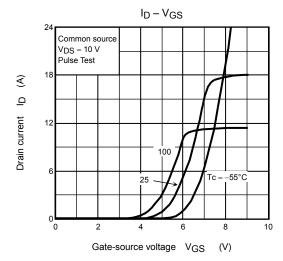


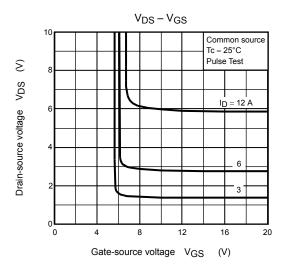
Note 4 : A line under a Lot No. identifies the indication of product Labels  $\hbox{[[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]}$ 

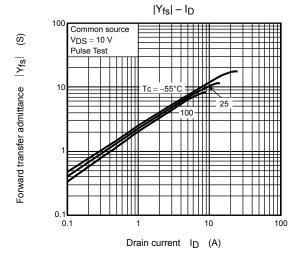
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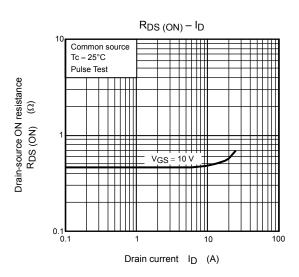


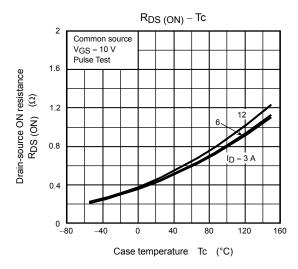


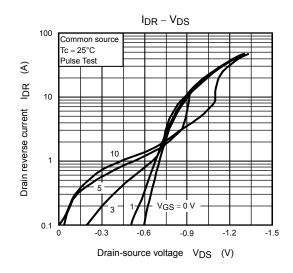


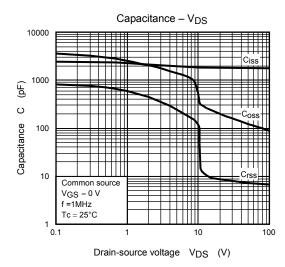


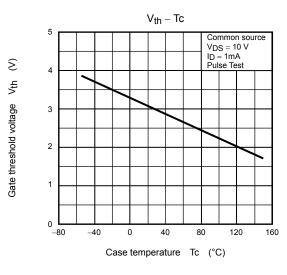


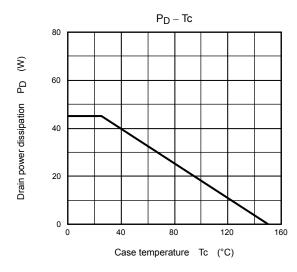


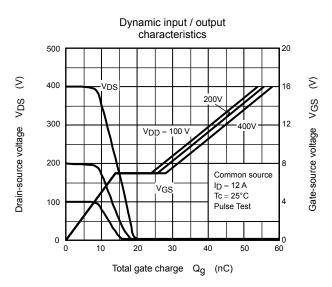


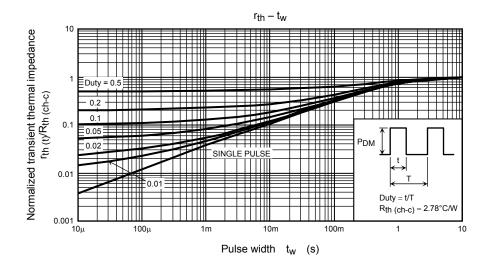


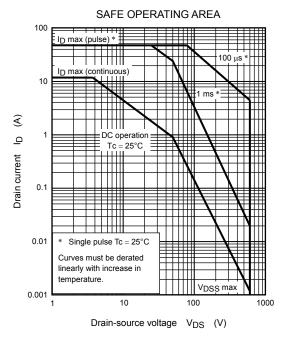


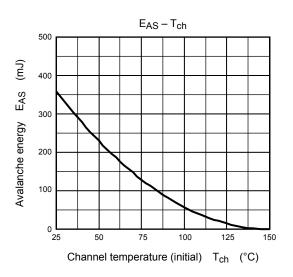


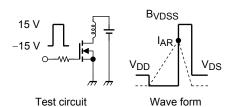












$$\begin{aligned} &R_G = 25~\Omega \\ &V_{DD} = 90~V,~L = 4.36~mH \end{aligned} \qquad \text{EAS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( -\frac{1}{10} \cdot \frac{1}{10} \cdot \frac{1}{$$

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